The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a reverse stagger type amorphous silicon thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region over said gate electrode with a gate insulating film interposed therebetween, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said reverse stagger type amorphous silicon thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween.

2. (Canceled)

3. (Previously Presented) A device according to claim 1 wherein said capacitive wiring is in parallel with said gate line.

4. (Canceled)

5. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line of n-th row provided over a substrate;

a gate line of (n+1)-th row provided over said substrate;

a gate line of (n+2)-th row provided over said substrate;

a data line of m-th column provided over said substrate;

a pixel electrode of n-th row and m-th column provided over said substrate and connected with said data line and said gate line of n-th row through corresponding at least one transistor; said pixel electrode overlapping said gate line of (n+1)-th row with an insulator therebetween and overlapping said gate line of n-th row with an insulator therebetween; and

a pixel electrode of (n+1)-th row and m-th column provided over said substrate and connected with said data line and said gate line of (n+1)-th row through corresponding at least one transistor, said pixel electrode of (n+1)-th row and m-th column overlapping said gate line of (n+2)-th row with an insulator therebetween and overlapping said gate line of (n+1)-th row with an insulator therebetween,

wherein said pixel electrode of n-th row and m-th column is provided on an opposite side of said data line to said pixel electrode of (n+1)-th row and m-th column.

6.-49. (Canceled)

50. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a reverse stagger type amorphous silicon thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region over said gate electrode with a gate insulating film interposed therebetween, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said reverse stagger type amorphous silicon thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a sum of a capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring is above ten times as large as a difference between the capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring.

51. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a reverse stagger type amorphous silicon thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region over said gate electrode with a gate insulating film interposed therebetween, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said reverse stagger type amorphous silicon thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a capacitance induced by an overlap between said data line and said transparent pixel electrode is smaller than the capacitances between the transparent pixel electrode and the gate line and the transparent pixel electrode and the capacitive wiring.

52. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a reverse stagger type amorphous silicon thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region over said gate electrode with a gate insulating film interposed therebetween, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said reverse stagger type amorphous silicon thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a sum of a capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring is above ten times as large as a difference between the capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring, and

wherein a capacitance induced by an overlap between said data line and said transparent pixel electrode is smaller than the capacitances between the transparent pixel electrode and the gate line and the transparent pixel electrode and the capacitive wiring.

53. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a reverse stagger type amorphous silicon thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region over said gate electrode with a gate insulating film interposed therebetween, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said reverse stagger type amorphous silicon thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring.

54. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a reverse stagger type amorphous silicon thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region over said gate electrode with a gate insulating film interposed therebetween, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said reverse stagger type amorphous silicon thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring, and

after the application of the first pulse is stopped, the application of the second pulse is stopped.

55. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a reverse stagger type amorphous silicon thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region over said gate electrode with a gate insulating film interposed therebetween, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said reverse stagger type amorphous silicon thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a sum of a capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring is above ten times as large as a difference between the capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring, and

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to the capacitive wiring.

56. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a reverse stagger type amorphous silicon thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region over said gate electrode with a gate insulating film interposed therebetween, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said reverse stagger type amorphous silicon thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring, and

wherein a capacitance induced by an overlap between said data line and said transparent pixel electrode is smaller than the capacitances between the transparent pixel electrode and the gate line and the transparent pixel electrode and the capacitive wiring.

57. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a reverse stagger type amorphous silicon thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region over said gate electrode with a gate insulating film interposed

therebetween, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said reverse stagger type amorphous silicon thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a sum of a capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring is above ten times as large as a difference between the capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring,

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring, and

wherein a capacitance induced by an overlap between said data line and said transparent pixel electrode is smaller than the capacitances between the transparent pixel electrode and the gate line and the transparent pixel electrode and the capacitive wiring.

58. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a reverse stagger type amorphous silicon thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a

channel region over said gate electrode with a gate insulating film interposed therebetween, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said reverse stagger type amorphous silicon thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a sum of a capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring is above ten times as large as a difference between the capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring,

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring, and

after the application of the first pulse is stopped, the application of the second pulse is stopped.

59. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a reverse stagger type amorphous silicon thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region over said gate electrode with a gate insulating film interposed

therebetween, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said reverse stagger type amorphous silicon thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a capacitance induced by an overlap between said data line and said transparent pixel electrode is smaller than the capacitances between the transparent pixel electrode and the gate line and the transparent pixel electrode and the capacitive wiring,

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring, and

after the application of the first pulse is stopped, the application of the second pulse is stopped.

60. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a reverse stagger type amorphous silicon thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region over said gate electrode with a gate insulating film interposed therebetween, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said reverse stagger type amorphous silicon thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a sum of a capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring is above ten times as large as a difference between the capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring,

wherein a capacitance induced by an overlap between said data line and said transparent pixel electrode is smaller than the capacitances between the transparent pixel electrode and the gate line and the transparent pixel electrode and the capacitive wiring,

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring, and

after the application of the first pulse is stopped, the application of the second pulse is stopped.

61. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and

a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween.

62. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a sum of a capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring is above ten times as large as a difference between the capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring.

63. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a capacitance induced by an overlap between said data line and said transparent pixel electrode is smaller than the capacitances between the transparent pixel electrode and the gate line and the transparent pixel electrode and the capacitive wiring.

64. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a sum of a capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring is above ten times as large as a difference between the capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring, and

wherein a capacitance induced by an overlap between said data line and said transparent pixel electrode is smaller than the capacitances between the transparent pixel electrode and the gate line and the transparent pixel electrode and the capacitive wiring.

65. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring.

66. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring, and

after the application of the first pulse is stopped, the application of the second pulse is stopped.

67. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a sum of a capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the

capacitive wiring is above ten times as large as a difference between the capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring, and

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to the capacitive wiring.

68. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring, and

wherein a capacitance induced by an overlap between said data line and said transparent pixel electrode is smaller than the capacitances between the transparent pixel electrode and the gate line and the transparent pixel electrode and the capacitive wiring.

69. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a sum of a capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring is above ten times as large as a difference between the capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring,

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring, and

wherein a capacitance induced by an overlap between said data line and said transparent pixel electrode is smaller than the capacitances between the transparent pixel electrode and the gate line and the transparent pixel electrode and the capacitive wiring.

70. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a sum of a capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring is above ten times as large as a difference between the capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring,

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring, and

after the application of the first pulse is stopped, the application of the second pulse is stopped.

71. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a capacitance induced by an overlap between said data line and said transparent pixel electrode is smaller than the capacitances between the transparent pixel electrode and the gate line and the transparent pixel electrode and the capacitive wiring,

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring, and

after the application of the first pulse is stopped, the application of the second pulse is stopped.

72. (Currently Amended) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating flattening film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said gate line and said ~~capacitance~~ capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a sum of a capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring is above ten times as large as a difference between the capacitance between the transparent pixel electrode and the gate line and the capacitance between the transparent pixel electrode and the capacitive wiring,

wherein a capacitance induced by an overlap between said data line and said transparent pixel electrode is smaller than the capacitances between the transparent pixel electrode and the gate line and the transparent pixel electrode and the capacitive wiring,

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring, and

after the application of the first pulse is stopped, the application of the second pulse is stopped.

73. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a pixel electrode provided over said insulating film wherein said pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said pixel electrode with said insulating film interposed therebetween,

wherein a sum of a capacitance between the pixel electrode and the gate line and the capacitance between the pixel electrode and the capacitive wiring is above ten times as large as a difference between the capacitance between the pixel electrode and the gate line and the capacitance between the pixel electrode and the capacitive wiring, and

wherein a capacitance induced by an overlap between said data line and said pixel electrode is smaller than the capacitances between the pixel electrode and the gate line and the pixel electrode and the capacitive wiring.

74. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a pixel electrode provided over said insulating film wherein said pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said pixel electrode with said insulating film interposed therebetween,

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring, and

after the application of the first pulse is stopped, the application of the second pulse is stopped.

75. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a pixel electrode provided over said insulating film wherein said pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said pixel electrode with said insulating film interposed therebetween,

wherein a sum of a capacitance between the pixel electrode and the gate line and the capacitance between the pixel electrode and the capacitive wiring is above ten times as large as a difference between the capacitance between the pixel electrode and the gate line and the capacitance between the pixel electrode and the capacitive wiring,

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring, and

after the application of the first pulse is stopped, the application of the second pulse is stopped.

76. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a pixel electrode provided over said insulating film wherein said pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said pixel electrode with said insulating film interposed therebetween,

wherein a capacitance induced by an overlap between said data line and said pixel electrode is smaller than the capacitances between the pixel electrode and the gate line and the pixel electrode and the capacitive wiring, and

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring.

77. (Previously Presented) An electro-optical device of an active matrix comprising:

a gate line provided over a substrate;

a data line provided over said substrate;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

a capacitive wiring provided over said substrate;

an insulating film over said gate line, said data line, said capacitive wiring and said thin film transistor;

a pixel electrode provided over said insulating film wherein said pixel electrode overlaps said gate line and said capacitive wiring and is electrically connected to the other of said source region and said drain region; and

a capacitance formed between said capacitive wiring and said pixel electrode with said insulating film interposed therebetween,

wherein a capacitance induced by an overlap between said data line and said pixel electrode is smaller than the capacitances between the pixel electrode and the gate line and the pixel electrode and the capacitive wiring, and

wherein when a first pulse is applied to the gate line, a second pulse having an opposite polarity to the first pulse is applied to said capacitive wiring, and

after the application of the first pulse is stopped, the application of the second pulse is stopped.

78. (Previously Presented) An electro-optical device of an active matrix comprising:

a first gate line and a second gate line extending in parallel provided over a substrate;

a data line provided over said substrate and extending across said first and second gate lines;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said first gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

an insulating flattening film over said first and second gate lines, said data line, and said thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said first and second gate lines and is electrically connected to the other of said source region and said drain region; and

a first capacitance formed between said first gate line and said transparent pixel electrode with said insulating flattening film interposed therebetween; and

a second capacitance formed between said second gate line and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a sum of the first and second capacitances is above ten times as large as a difference between the first and second capacitances.

79. (Previously Presented) An electro-optical device of an active matrix comprising:

a first gate line and a second gate line extending in parallel provided over a substrate;

a data line provided over said substrate and extending across said first and second gate lines;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said first gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

an insulating flattening film over said first and second gate lines, said data line, and said thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said first and second gate lines and is electrically connected to the other of said source region and said drain region; and

a first capacitance formed between said first gate line and said transparent pixel electrode with said insulating flattening film interposed therebetween; and

a second capacitance formed between said second gate line and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a sum of the first and second capacitances is above ten times as large as a difference between the first and second capacitances,

wherein a capacitance induced by an overlap between said data line and said transparent pixel electrode is smaller than the first and second capacitances.

80. (Previously Presented) An electro-optical device of an active matrix comprising:

a first gate line and a second gate line extending in parallel provided over a substrate;

a data line provided over said substrate and extending across said first and second gate lines;

a thin film transistor provided over said substrate and comprising a gate electrode electrically connected to said first gate line, a channel region, a source region and a drain region wherein one of said source region and said drain region is electrically connected to said data line;

an insulating flattening film over said first and second gate lines, said data line, and said thin film transistor;

a transparent pixel electrode provided over said insulating flattening film wherein said transparent pixel electrode overlaps said first and second gate lines and is electrically connected to the other of said source region and said drain region; and

a first capacitance formed between said first gate line and said transparent pixel electrode with said insulating flattening film interposed therebetween; and

a second capacitance formed between said second gate line and said transparent pixel electrode with said insulating flattening film interposed therebetween,

wherein a sum of the first and second capacitances is above ten times as large as a difference between the first and second capacitances, and

wherein a capacitance induced by an overlap between said data line and said transparent pixel electrode is smaller than the first and second capacitances.

81. (Previously Presented) An active-matrix device comprising:

a substrate having an insulating surface;

first and second pixel electrodes arranged in a first column over said substrate;

a third pixel electrode arranged in a second column over said substrate, each of said first, second and third pixel electrodes being provided with at least one thin film transistor;

first, second and third gate lines extending in parallel over said substrate,

wherein said first gate line drives the thin film transistor associated with said first pixel electrode and said first pixel electrode overlaps said first gate line to form a first capacitance therebetween;

said second gate line drives the thin film transistor associated with the third pixel electrode and extends below said first pixel electrode to form a second capacitance between said second gate line and said first pixel electrode;

said third gate line drives the thin film transistor associated with the second pixel electrode and extends below said third pixel electrode to form a third capacitance between said third gate line and said third pixel electrode,

wherein a sum of the first and second capacitances is above ten times as large as a difference between the first and second capacitances.

82. (Previously Presented) An active-matrix device comprising:

a substrate having an insulating surface;

first and second pixel electrodes arranged in a first column over said substrate;

a third pixel electrode arranged in a second column over said substrate, each of said first, second and third pixel electrodes being provided with at least one thin film transistor;

first, second and third gate lines extending in parallel over said substrate,

first and second data lines extending across the first, second and third gate lines wherein said first data line is connected to the thin film transistor associated with the first pixel electrode,

wherein said first gate line drives the thin film transistor associated with said first pixel electrode and said first pixel electrode overlaps said first gate line to form a first capacitance therebetween;

said second gate line drives the thin film transistor associated with the third pixel electrode and extends below said first pixel electrode to form a second capacitance between said second gate line and said first pixel electrode;

said third gate line drives the thin film transistor associated with the second pixel electrode and extends below said third pixel electrode to form a third capacitance between said third gate line and said third pixel electrode,

a capacitance induced by an overlap between said first data line and said first pixel electrode is smaller than the first and second capacitances.

83. (Previously Presented) An active-matrix device comprising:

a substrate having an insulating surface;

first and second pixel electrodes arranged in a first column over said substrate;

a third pixel electrode arranged in a second column over said substrate, each of said first, second and third pixel electrodes being provided with at least one thin film transistor;

first, second and third gate lines extending in parallel over said substrate,

first and second data lines extending across the first, second and third gate lines wherein said first data line is connected to the thin film transistor associated with the first pixel electrode,

wherein said first gate line drives the thin film transistor associated with said first pixel electrode and said first pixel electrode overlaps said first gate line to form a first capacitance therebetween;

said second gate line drives the thin film transistor associated with the third pixel electrode and extends below said first pixel electrode to form a second capacitance between said second gate line and said first pixel electrode;

said third gate line drives the thin film transistor associated with the second pixel electrode and extends below said third pixel electrode to form a third capacitance between said third gate line and said third pixel electrode,

a sum of the first and second capacitances is above ten times as large as a difference between the first and second capacitances, and

a capacitance induced by an overlap between said first data line and said first pixel electrode is smaller than the first and second capacitances.

84. (Previously Presented) The electro-optical device of claim 73, wherein the pixel electrode is transparent.

85. (Previously Presented) The electro-optical device of claim 74, wherein the pixel electrode is transparent.

86. (Previously Presented) The electro-optical device of claim 75, wherein the pixel electrode is transparent.

87. (Previously Presented) The electro-optical device of claim 76, wherein the pixel electrode is transparent.

88. (Previously Presented) The electro-optical device of claim 77, wherein the pixel electrode is transparent.

89. (Previously Presented) The electro-optical device of claim 75, wherein a capacitance induced by an overlap between said data line and said pixel electrode is smaller than the capacitances between the pixel electrode and the gate line and the pixel electrode and the capacitive wiring.

90. (Previously Presented) The electro-optical device of claim 76, wherein a sum of a capacitance between the pixel electrode and the gate line and the capacitance between the pixel electrode and the capacitive wiring is above ten times as large as a difference between the capacitance between the pixel electrode and the gate line and the capacitance between the pixel electrode and the capacitive wiring.

91. (Previously Presented) The electro-optical device of claim 77, wherein a sum of a capacitance between the pixel electrode and the gate line and the capacitance between the pixel electrode and the capacitive wiring is above ten times as large as a difference between the capacitance between the pixel electrode and the gate line and the capacitance between the pixel electrode and the capacitive wiring.

92. (Previously Presented) The electro-optical device of claim 78, wherein the thin film transistor is a reverse stagger type amorphous silicon thin film transistor.

93. (Previously Presented) The electro-optical device of claim 79, wherein the thin film transistor is a reverse stagger type amorphous silicon thin film transistor.

94. (Previously Presented) The electro-optical device of claim 80, wherein the thin film transistor is a reverse stagger type amorphous silicon thin film transistor.

95. (Previously Presented) The electro-optical device of claim 50, wherein the insulating flattening film comprises polyimide.

96. (Previously Presented) The electro-optical device of claim 51, wherein the insulating flattening film comprises polyimide.

97. (Previously Presented) The electro-optical device of claim 52, wherein the insulating flattening film comprises polyimide.

98. (Previously Presented) The electro-optical device of claim 53, wherein the insulating flattening film comprises polyimide.

99. (Previously Presented) The electro-optical device of claim 54, wherein the insulating flattening film comprises polyimide.

100. (Previously Presented) The electro-optical device of claim 55, wherein the insulating flattening film comprises polyimide.

101. (Previously Presented) The electro-optical device of claim 56, wherein the insulating flattening film comprises polyimide.

102. (Previously Presented) The electro-optical device of claim 57, wherein the insulating flattening film comprises polyimide.

103. (Previously Presented) The electro-optical device of claim 58, wherein the insulating flattening film comprises polyimide.

104. (Previously Presented) The electro-optical device of claim 59, wherein the insulating flattening film comprises polyimide.

105. (Previously Presented) The electro-optical device of claim 60, wherein the insulating flattening film comprises polyimide.

106. (Previously Presented) The electro-optical device of claim 61, wherein the insulating flattening film comprises polyimide.

107. (Previously Presented) The electro-optical device of claim 62, wherein the insulating flattening film comprises polyimide.

108. (Previously Presented) The electro-optical device of claim 63, wherein the insulating flattening film comprises polyimide.

109. (Previously Presented) The electro-optical device of claim 64, wherein the insulating flattening film comprises polyimide.

110. (Previously Presented) The electro-optical device of claim 65, wherein the insulating flattening film comprises polyimide.

111. (Previously Presented) The electro-optical device of claim 66, wherein the insulating flattening film comprises polyimide.

112. (Previously Presented) The electro-optical device of claim 67, wherein the insulating flattening film comprises polyimide.

113. (Previously Presented) The electro-optical device of claim 68, wherein the insulating flattening film comprises polyimide.

114. (Previously Presented) The electro-optical device of claim 69, wherein the insulating flattening film comprises polyimide.

115. (Previously Presented) The electro-optical device of claim 70, wherein the insulating flattening film comprises polyimide.

116. (Previously Presented) The electro-optical device of claim 71, wherein the insulating flattening film comprises polyimide.

117. (Previously Presented) The electro-optical device of claim 72, wherein the insulating flattening film comprises polyimide.

118. (Previously Presented) The electro-optical device of claim 78, wherein the insulating flattening film comprises polyimide.

119. (Previously Presented) The electro-optical device of claim 79, wherein the insulating flattening film comprises polyimide.

120. (Previously Presented) The electro-optical device of claim 80, wherein the insulating flattening film comprises polyimide.

121. (New) An electro-optical device of an active matrix comprising:

a gate line of n-th row provided over a substrate;

a gate line of (n+1)-th row provided over said substrate;

a data line of m-th column provided over said substrate;

a first pixel electrode provided over said substrate and electrically connected with said data line and said gate line of n-th row through at least one transistor; and

a second pixel electrode provided over said substrate and electrically connected with said data line and said gate line of (n+1)-th row through at least one transistor,

wherein said first pixel electrode is provided on an opposite side of said data line to said second pixel electrode,

wherein a first bipolar pulse is applied to the gate line of n-th row during a first period, a second bipolar pulse is applied to the gate line of (n+1)-th row during a second period, and the second period appears later than and partly overlaps the first period, and

wherein each of the first and second bipolar pulses includes a first pulse and a second pulse having an opposite polarity to the first pulse.

122. (New) The electro-optical device according to claim 121 wherein the first pulse has a negative potential and the second pulse has a positive potential.

123. (New) The electro-optical device according to claim 121 wherein the second pulse appears after the first pulse without an interruption.

124. (New) The electro-optical device according to claim 121 wherein the first pixel electrode overlaps the gate line of n-th row and the gate line of (n+1)-th row.

125. (New) An electro-optical device of an active matrix comprising:

a gate line of n-th row provided over a substrate;

a gate line of (n+1)-th row provided over said substrate;

a data line of m-th column provided over said substrate;

a first pixel electrode provided over said substrate and electrically connected with said data line and said gate line of n-th row through at least one transistor; and

a second pixel electrode provided over said substrate and electrically connected with said data line and said gate line of (n+1)-th row through at least one transistor,

wherein said first pixel electrode is provided on an opposite side of said data line to said second pixel electrode,

wherein a bipolar pulse is applied to the gate line of n-th row, and

wherein the bipolar pulse includes a first pulse and a second pulse having an opposite polarity to the first pulse.

126. (New) The electro-optical device according to claim 125 wherein the first pulse has a negative potential and the second pulse has a positive potential.

127. (New) The electro-optical device according to claim 125 wherein the first pixel electrode overlaps the gate line of n-th row and the gate line of (n+1)-th row.

128. (New) The electro-optical device according to claim 125 wherein the second pulse appears after the first pulse without an interruption.

129. (New) An electro-optical device of an active matrix comprising:

a gate line of n-th row provided over a substrate;

a gate line of (n+1)-th row provided over said substrate;

a data line of m-th column provided over said substrate;

a first reverse stagger type amorphous silicon thin film transistor having a gate electrode electrically connected to the gate line of n-th row and source and drain regions wherein one of the source and drain regions is electrically connected to the data line;

a second reverse stagger type amorphous silicon thin film transistor having a gate electrode electrically connected to the gate line of (n+1)-th row and source and drain regions wherein one of the source and drain regions is electrically connected to the data line;

an insulating film formed over the first and second reverse stagger type amorphous silicon thin film transistors;

a first pixel electrode provided over said insulating film and electrically connected with the other one of the source and drain regions of the first reverse stagger type amorphous silicon thin film transistor; and

a second pixel electrode provided over said insulating film and electrically connected with the other one of the source and drain regions of the second reverse stagger type amorphous silicon thin film transistor,

wherein said first pixel electrode is provided on an opposite side of said data line to said second pixel electrode,

wherein a first bipolar pulse is applied to the gate line of n-th row during a first period, a second bipolar pulse is applied to the gate line of (n+1)-th row during a second period, and the second period appears later than and partly overlaps the first period, and

wherein each of the first and second bipolar pulses includes a first pulse and a second pulse having an opposite polarity to the first pulse.

130. (New) The electro-optical device according to claim 129 wherein the first pulse has a negative potential and the second pulse has a positive potential.

131. (New) The electro-optical device according to claim 129 wherein the second pulse appears after the first pulse without an interruption.

132. (New) The electro-optical device according to claim 129 wherein the first pixel electrode overlaps the gate line of n-th row and the gate line of (n+1)-th row.

133. (New) An electro-optical device of an active matrix comprising:

a gate line of n-th row provided over a substrate;

a gate line of (n+1)-th row provided over said substrate;

a data line of m-th column provided over said substrate;

a first thin film transistor having a gate electrode electrically connected to the gate line of n-th row, a channel region and source and drain regions wherein one of the source and drain regions is electrically connected to the data line;

a second thin film transistor having a gate electrode electrically connected to the gate line of (n+1)-th row and source and drain regions wherein one of the source and drain regions is electrically connected to the data line;

an insulating flattening film formed over the first and second thin film transistors;

a first pixel electrode provided over said insulating film and electrically connected with the other one of the source and drain regions of the thin film transistor; and

a second pixel electrode provided over said insulating film and electrically connected with the other one of the source and drain regions of the second thin film transistor,

wherein said first pixel electrode is provided on an opposite side of said data line to said second pixel electrode,

wherein a first bipolar pulse is applied to the gate line of n-th row during a first period, a second bipolar pulse is applied to the gate line of (n+1)-th row during a second period, and the second period appears later than and partly overlaps the first period, and

wherein each of the first and second bipolar pulses includes a first pulse and a second pulse having an opposite polarity to the first pulse.

134. (New) The electro-optical device according to claim 133 wherein the first pulse has a negative potential and the second pulse has a positive potential.

135. (New) The electro-optical device according to claim 133 wherein the second pulse appears after the first pulse without an interruption.

136. (New) The electro-optical device according to claim 133 wherein the first pixel electrode overlaps the gate line of n-th row and the gate line of (n+1)-th row.

137. (New) An electro-optical device of an active matrix comprising:

a gate line of n-th row provided over a substrate;

a gate line of (n+1)-th row provided over said substrate;

a data line of m-th column provided over said substrate;

a first reverse stagger type amorphous silicon thin film transistor having a gate electrode electrically connected to the gate line of n-th row and source and drain regions wherein one of the source and drain regions is electrically connected to the data line;

a second reverse stagger type amorphous silicon thin film transistor having a gate electrode electrically connected to the gate line of (n+1)-th row and source and drain regions wherein one of the source and drain regions is electrically connected to the data line;

an insulating film formed over the first and second reverse stagger type amorphous silicon thin film transistors;

a first pixel electrode provided over said insulating film and electrically connected with the other one of the source and drain regions of the first reverse stagger type amorphous silicon thin film transistor; and

a second pixel electrode provided over said insulating film and electrically connected with the other one of the source and drain regions of the second reverse stagger type amorphous silicon thin film transistor,

wherein said first pixel electrode is provided on an opposite side of said data line to said second pixel electrode.

138. (New) The electro-optical device according to claim 137 wherein the first pixel electrode overlaps the gate line of n-th row and the gate line of (n+1)-th row.

139. (New) An electro-optical device of an active matrix comprising:

a gate line of n-th row provided over a substrate;

a gate line of (n+1)-th row provided over said substrate;

a data line of m-th column provided over said substrate;

a first thin film transistor having a gate electrode electrically connected to the gate line of n-th row and source and drain regions wherein one of the source and drain regions is electrically connected to the data line;

a second thin film transistor having a gate electrode electrically connected to the gate line of (n+1)-th row and source and drain regions wherein one of the source and drain regions is electrically connected to the data line;

an insulating flattening film formed over the first and second thin film transistors;

a first pixel electrode provided over said insulating film and electrically connected with the other one of the source and drain regions of the thin film transistor; and

a second pixel electrode provided over said insulating film and electrically connected with the other one of the source and drain regions of the second thin film transistor,

wherein said first pixel electrode is provided on an opposite side of said data line to said second pixel electrode.

140. (New) The electro-optical device according to claim 139 wherein the first pixel electrode overlaps the gate line of n-th row and the gate line of (n+1)-th row.

141. (New) The electro-optical device according to claim 139 wherein each of the first and second thin film transistor is a reverse stagger amorphous silicon thin film transistor.

142. (New) An electro-optical device of an active matrix comprising:

a gate line of n-th row provided over a substrate;

a gate line of (n+1)-th row provided over said substrate;

a data line of m-th column provided over said substrate;

a first pixel electrode provided over said substrate and electrically connected with said data line and said gate line of n-th row through at least one transistor; and

a second pixel electrode provided over said substrate and electrically connected with said data line and said gate line of (n+1)-th row through at least one transistor,

wherein a first bipolar pulse is applied to the gate line of n-th row during a first period, a second bipolar pulse is applied to the gate line of (n+1)-th row during a second period, and the second period appears later than and partly overlaps the first period,

wherein each of the first and second bipolar pulses includes a first pulse and a second pulse having an opposite polarity to the first pulse, and

wherein a pulse width of the first pulse is different from a pulse width of the second pulse.

143. (New) The electro-optical device according to claim 142 wherein said first pixel electrode is provided on an opposite side of said data line to said second pixel electrode,

144. (New) The electro-optical device according to claim 142 wherein the first pulse has a negative potential and the second pulse has a positive potential.

145. (New) The electro-optical device according to claim 142 wherein the second pulse appears after the first pulse without an interruption.

146. (New) The electro-optical device according to claim 142 wherein the first pixel electrode overlaps the gate line of n-th row and the gate line of (n+1)-th row.

147. (New) The electro-optical device according to claim 142 wherein the pulse width of the first pulse is longer than the pulse width of the second pulse.

148. (New) An electro-optical device of an active matrix comprising:

a gate line of n-th row provided over a substrate;

a gate line of (n+1)-th row provided over said substrate;

a data line of m-th column provided over said substrate;

a first pixel electrode provided over said substrate and electrically connected with said data line and said gate line of n-th row through at least one transistor; and

a second pixel electrode provided over said substrate and electrically connected with said data line and said gate line of (n+1)-th row through at least one transistor,

wherein a bipolar pulse is applied to the gate line of n-th row, and

wherein the bipolar pulse includes a first pulse and a second pulse having an opposite polarity to the first pulse, and

wherein a pulse width of the first pulse is different from a pulse width of the second pulse.

149. (New) The electro-optical device according to claim 148 wherein said first pixel electrode is provided on an opposite side of said data line to said second pixel electrode,

150. (New) The electro-optical device according to claim 148 wherein the first pulse has a negative potential and the second pulse has a positive potential.

151. (New) The electro-optical device according to claim 148 wherein the first pixel electrode overlaps the gate line of n-th row and the gate line of (n+1)-th row.

152. (New) The electro-optical device according to claim 148 wherein the second pulse appears after the first pulse without an interruption.

153. (New) An electro-optical device of an active matrix comprising:

a gate line of n-th row provided over a substrate;

a gate line of (n+1)-th row provided over said substrate;

a data line of m-th column provided over said substrate;

a first thin film transistor having a gate electrode electrically connected to the gate line of n-th row, a channel region and source and drain regions wherein one of the source and drain regions is electrically connected to the data line;

a second thin film transistor having a gate electrode electrically connected to the gate line of (n+1)-th row and source and drain regions wherein one of the source and drain regions is electrically connected to the data line;

an insulating flattening film formed over the first and second thin film transistors;

a first pixel electrode provided over said insulating film and electrically connected with the other one of the source and drain regions of the thin film transistor; and

a second pixel electrode provided over said insulating film and electrically connected with the other one of the source and drain regions of the second thin film transistor,

wherein a first bipolar pulse is applied to the gate line of n-th row during a first period, a second bipolar pulse is applied to the gate line of (n+1)-th row during a second period, and the second period appears later than and partly overlaps the first period,

wherein each of the first and second bipolar pulses includes a first pulse and a second pulse having an opposite polarity to the first pulse, and

wherein a pulse width of the first pulse is different from a pulse width of the second pulse.

154. (New) The electro-optical device according to claim 153 wherein said first pixel electrode is provided on an opposite side of said data line to said second pixel electrode.

155. (New) The electro-optical device according to claim 153 wherein the first pulse has a negative potential and the second pulse has a positive potential.

156. (New) The electro-optical device according to claim 153 wherein the second pulse appears after the first pulse without an interruption.

157. (New) The electro-optical device according to claim 153 wherein the first pixel electrode overlaps the gate line of n-th row and the gate line of (n+1)-th row.

158. (New) The electro-optical device according to claim 153 wherein each of the first and second thin film transistors is a reverse stagger amorphous silicon thin film transistor.